

Silicon PNP Power Transistors

2SA633

DESCRIPTION

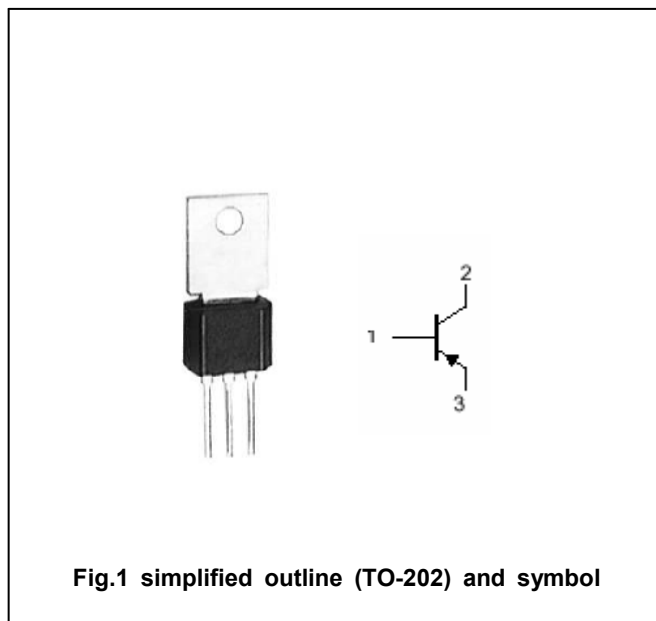
- With TO-202 package
- High current capability

APPLICATIONS

- Power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-30	V
V_{CEO}	Collector-emitter voltage	Open base	-30	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-2	A
I_{CM}	Collector current-peak		-3	A
I_B	Base current		-0.6	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	10	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-10mA; I_B=0$	-30			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-0.1mA; I_C=0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-1.5A; I_B=-0.15A$			-1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-2A; I_B=-0.2A$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-20V; I_E=0$			-1	μA
I_{CEO}	Collector cut-off current	$V_{CE}=-12V; I_B=0$			-100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-3V; I_C=0$			-1	μA
h_{FE-1}	DC current gain	$I_C=-20mA; V_{CE}=-5V$	20			
h_{FE-2}	DC current gain	$I_C=-1A; V_{CE}=-5V$	80		250	
f_T	Transition frequency	$I_C=-0.1A; V_{CE}=-5V$		60		MHz

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PACKAGE OUTLINE

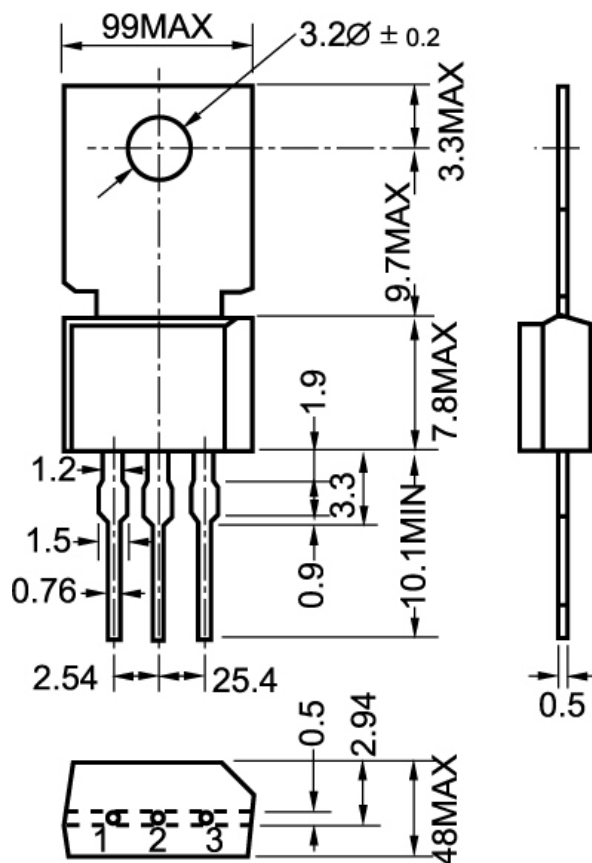


Fig.2 outline dimensions